

# Akinobu Teramoto

## List of Publications by Year in descending order

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274  
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331670

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276  
docs citations

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times ranked

1180  
citing authors

#	ARTICLE	IF	CITATIONS
1	Adsorption and surface reaction of isopropyl alcohol on SiO <sub>2</sub> surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 053201.	2.1	0
2	Impact on the Conductance Method of the Asymmetry in the AC Response Induced by Interface Trap Levels. ECS Journal of Solid State Science and Technology, 2021, 10, 043004.	1.8	0
3	A high-precision current measurement platform applied for statistical measurement of discharge current transient spectroscopy of traps in SiN dielectrics. Japanese Journal of Applied Physics, 2021, 60, 086501.	1.5	0
4	Evaluation of Low-Frequency Noise in MOSFETs Used as a Key Component in Semiconductor Memory Devices. Electronics (Switzerland), 2021, 10, 1759.	3.1	7
5	Plasma resistance of sintered and ion-plated yttrium oxyfluorides with various Y, O, and F composition ratios for use in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	5
6	Study on Influence of O <sub>2</sub> Concentration in Wafer Cleaning Ambient for Smoothness of Silicon (110) Surface Appearing at Sidewall of Three-Dimensional Transistors. ECS Transactions, 2020, 97, 23-29.	0.5	0
7	Resistance Measurement Platform for Statistical Analysis of Emerging Memory Materials. IEEE Transactions on Semiconductor Manufacturing, 2020, 33, 232-239.	1.7	2
8	Influence of silicon wafer surface roughness on semiconductor device characteristics. Japanese Journal of Applied Physics, 2020, 59, SMMB06.	1.5	13
9	Effect of Drain-to-Source Voltage on Random Telegraph Noise Based on Statistical Analysis of MOSFETs with Various Gate Shapes. , 2020, , .		3
10	High reliability CoFeB/MgO/CoFeB magnetic tunnel junction fabrication using low-damage ion beam etching. Japanese Journal of Applied Physics, 2020, 59, SGGB05.	1.5	2
11	Control of ion-flux and ion-energy in direct inductively coupled plasma reactor for interfacial-mixing plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 032408.	2.1	4
12	A high-precision 1 $\times$ 10 <sup>-10</sup> $\Omega$ range resistance measurement platform for statistical evaluation of emerging memory materials. Japanese Journal of Applied Physics, 2020, 59, SGGL03.	1.5	1
13	Impact of CoFeB surface roughness on reliability of MgO films in CoFeB/MgO/CoFeB magnetic tunnel junction. Japanese Journal of Applied Physics, 2019, 58, SIIB29.	1.5	3
14	SiNx Deposition at Low Temperature Using UV-Irradiated NH <sub>3</sub> . ECS Transactions, 2019, 89, 31-36.	0.5	0
15	Resistance Measurement Platform for Statistical Analysis of Next Generation Memory Materials. , 2019, , .		3
16	Low-Temperature Deposition of Silicon Nitride Films Using Ultraviolet-Irradiated Ammonia. ECS Journal of Solid State Science and Technology, 2019, 8, P715-P718.	1.8	0
17	Monte Carlo Simulation of Nanowires Array Biosensor With AC Electroosmosis. IEEE Transactions on Electron Devices, 2018, 65, 1932-1938.	3.0	2
18	Experimental investigation of localized stress-induced leakage current distribution in gate dielectrics using array test circuit. Japanese Journal of Applied Physics, 2018, 57, 04FE11.	1.5	0

#	ARTICLE	IF	CITATIONS
19	An Electrical Impedance Biosensor Array for Tracking Moving Cells. , 2018, , .		2
20	Effect of drain current on appearance probability and amplitude of random telegraph noise in low-noise CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 04FF08.	1.5	4
21	Statistical Analysis of Threshold Voltage Variation Using MOSFETs With Asymmetric Source and Drain. IEEE Electron Device Letters, 2018, 39, 1836-1839.	3.9	2
22	Reliability of MgO in magnetic tunnel junctions formed by MgO sputtering and Mg oxidation. , 2018, , .		1
23	[Papers] Statistical Analyses of Random Telegraph Noise in Pixel Source Follower with Various Gate Shapes in CMOS Image Sensor. ITE Transactions on Media Technology and Applications, 2018, 6, 163-170.	0.5	5
24	[Papers] Impacts of Random Telegraph Noise with Various Time Constants and Number of States in Temporal Noise of CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2018, 6, 171-179.	0.5	4
25	Stable yttrium oxyfluoride used in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	29
26	Performances of accumulation-mode n- and p-MOSFETs on Si(110) wafers. Japanese Journal of Applied Physics, 2017, 56, 04CD15.	1.5	5
27	Formation technology of flat surface with epitaxial growth on ion-implanted (100)-oriented Si surface of thin silicon-on-insulator. Japanese Journal of Applied Physics, 2017, 56, 105503.	1.5	0
28	Atomically flat interface for noise reduction in SOI-MOSFETs. , 2017, , .		0
29	Hole-Trapping Process at Al <sub>2</sub> O <sub>3</sub> /GaN Interface Formed by Atomic Layer Deposition. IEEE Electron Device Letters, 2017, 38, 1309-1312.	3.9	4
30	Impact of SiO <sub>2</sub> /Si interface micro-roughness on SILC distribution and dielectric breakdown: A comparative study with atomically flattened devices. , 2017, , .		3
31	Monte-Carlo simulation of biomolecules' fluid-dynamics in electrolyte facing nanowires biosensor. , 2017, , .		2
32	Introduction of Atomically Flattening of Si Surface to Large-Scale Integration Process Employing Shallow Trench Isolation. ECS Journal of Solid State Science and Technology, 2016, 5, P67-P72.	1.8	5
33	Effects of Oxygen Microbubbles on Photoresist Layers under Hot Water Conditions. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2016, 29, 643-646.	0.3	2
34	Detection of short range order in SiO <sub>2</sub> thin-films by grazing-incidence wide and small-angle X-ray scattering. Journal of Applied Physics, 2016, 119, 154103.	2.5	1
35	Proposal of tunneling- and diffusion-current hybrid MOSFET: A device simulation study. Japanese Journal of Applied Physics, 2016, 55, 04ED12.	1.5	1
36	Impact of doping concentration on 1/f noise performances of accumulation-mode Si(100) n-MOSFETs. Japanese Journal of Applied Physics, 2016, 55, 04ED08.	1.5	3

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37	Oxidizing Species Dependence of the Interface Reaction during Atomic-Layer-Deposition Process and Post-Deposition-Anneal. ECS Transactions, 2016, 75, 207-214.	0.5	1
38	Evaluating Work-Function and Composition of ErSix on Various Surface Orientation of Silicon. ECS Journal of Solid State Science and Technology, 2016, 5, P608-P613.	1.8	1
39	Low Leakage Current Al <sub>2</sub> O <sub>3</sub> Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O <sub>2</sub> Post Deposition Annealing. ECS Transactions, 2016, 72, 91-100.	0.5	12
40	Introduction of a High Selectivity Etching Process with Advanced SiN <sub>x</sub> Etch Gas in the Fabrication of FinFET Structures. ECS Transactions, 2016, 72, 23-30.	0.5	1
41	Random telegraph noise measurement and analysis based on arrayed test circuit toward high S/N CMOS image sensors. , 2016, , .		12
42	Low Interface Trap Density and High Breakdown Electric Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2016, 63, 1795-1801.	3.0	6
43	Atomically flattening of Si surface of silicon on insulator and isolation-patterned wafers. Japanese Journal of Applied Physics, 2015, 54, 04DA04.	1.5	9
44	Structural Analyses of Thin SiO <sub>2</sub> Films Formed by Thermal Oxidation of Atomically Flat Si Surface by Using Synchrotron Radiation X-Ray Characterization. ECS Journal of Solid State Science and Technology, 2015, 4, N96-N98.	1.8	5
45	Effect of Process Temperature of Al <sub>2</sub> O <sub>3</sub> Atomic Layer Deposition Using Accurate Process Gasses Supply System. ECS Transactions, 2015, 66, 305-314.	0.5	1
46	Drastic suppression of the 1/f noise in MOSFETs: Fundamental fluctuations of mobility rather than induced mobility fluctuations. , 2015, , .		0
47	Flattening Technique of (551) Silicon Surface Using Xe/H <sub>2</sub> Plasma. ECS Transactions, 2014, 61, 401-407.	0.5	1
48	High Selectivity in Dry Etching of Silicon Nitride over Si Using a Novel Hydrofluorocarbon Etch Gas in a Microwave Excited Plasma for FinFET. ECS Transactions, 2014, 61, 29-37.	0.5	3
49	Demonstrating individual leakage path from random telegraph signal of stress induced leakage current. , 2014, , .		1
50	Effect of Composition Ratio on Erbium Silicide Work Function on Different Morphology of Si(100) Surface Changed by Alkaline Etching. ECS Transactions, 2014, 61, 47-53.	0.5	0
51	Mass densification and defect restoration in chemical vapor deposition silicon dioxide film using Ar plasma excited by microwave. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 051502.	2.1	3
52	Extraction of time constants ratio over nine orders of magnitude for understanding random telegraph noise in metal-oxide-semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC19.	1.5	13
53	Carrier mobility characteristics of (100), (110), and (551) oriented atomically flattened Si surfaces for fin structure design of multi-gate metal-insulator-silicon field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC04.	1.5	3
54	A novel analysis of oxide breakdown based on dynamic observation using ultra-high speed video capturing up to 10,000,000 frames per second. , 2014, , .		2

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55	Analyzing correlation between multiple traps in RTN characteristics. , 2014, , .		15
56	A statistical evaluation of effective time constants of random telegraph noise with various operation timings of in-pixel source follower transistors. Proceedings of SPIE, 2014, , .	0.8	1
57	Low-Interface-Trap-Density and High-Breakdown-Electric-Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2013, 60, 1916-1922.	3.0	9
58	Stress induced leakage current generated by hot-hole injection. Microelectronic Engineering, 2013, 109, 298-301.	2.4	1
59	A Test Circuit for Extremely Low Gate Leakage Current Measurement of 10 nA for 80 000 MOSFETs in 80 nm. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 288-295.	1.7	3
60	1/f Noise of accumulation mode p- and n-MOSFETs. , 2013, , .		2
61	A Statistical Evaluation of Random Telegraph Noise of In-Pixel Source Follower Equivalent Surface and Buried Channel Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3555-3561.	3.0	25
62	Angle-resolved photoelectron spectroscopy study on interfacial transition layer and oxidation-induced residual stress in Si(100) substrate near the interface. Microelectronic Engineering, 2013, 109, 197-199.	2.4	1
63	High Integrity SiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Gate Stack for Normally-off GaN MOSFET. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
64	Comprehensive Study on Chemical Structures of Compositional Transition Layer at SiO <sub>2</sub> /Si(100) Interface. ECS Transactions, 2013, 50, 313-318.	0.5	0
65	High Quality SiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Gate Stack for GaN Metal-Oxide-Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2013, 52, 04CF09.	1.5	37
66	Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species. Japanese Journal of Applied Physics, 2013, 52, 031302.	1.5	9
67	Effect of Erbium Silicide Crystallinity for Low Barrier Contact between Erbium Silicide and n-type Silicon. ECS Transactions, 2013, 50, 343-348.	0.5	0
68	Demonstrating distribution of SILC values at individual leakage spots. , 2013, , .		6
69	Schottky Barrier Height between Erbium Silicide and Various Morphology of Si(100) Surface Changed by Alkaline Etching. ECS Transactions, 2013, 58, 349-354.	0.5	0
70	High-speed and highly accurate evaluation of electrical characteristics in MOSFETs. , 2013, , .		4
71	The study of time constant analysis in random telegraph noise at the subthreshold voltage region. , 2013, , .		13
72	High Performance Normally-off GaN MOSFETs on Si Substrates. ECS Transactions, 2013, 58, 155-166.	0.5	2

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73	Effect of Composition Rate on Erbium Silicide Work Function on Different Silicon Surface Orientation. ECS Transactions, 2013, 53, 343-350.	0.5	0
74	XPS analysis of the terminated bonding states at GaN surface after chemical and plasma treatments. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1557-1560.	0.8	3
75	A statistical evaluation of low frequency noise of in-pixel source follower-equivalent transistors with various channel types and body bias. Proceedings of SPIE, 2013, , .	0.8	2
76	High Integrity SiO <sub>2</sub> Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaIn/GaN Hybrid Metal-Oxide Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	1.5	7
77	Electrical Properties of Silicon Nitride Using High Density and Low Plasma Damage PECVD Formed at 400°C. ECS Transactions, 2012, 45, 421-428.	0.5	3
78	Low Work Function between Erbium Silicide and n-type Silicon Controlled by Cap Film Stress. ECS Transactions, 2012, 45, 371-378.	0.5	0
79	Advanced Direct-Polishing Process Development of Non-Porous Ultralow-k Dielectric Fluorocarbon with Plasma Treatment on Cu Interconnects. Journal of the Electrochemical Society, 2012, 159, H407-H411.	2.9	5
80	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	1.5	1
81	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow-k Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	1.5	1
82	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	1.5	4
83	Hole Mobility in Accumulation Mode Metal-Oxide Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DC07.	1.5	8
84	Influence of Forming Gas Annealing on SiO <sub>2</sub> /Si(100) Interface Structures Formed Utilizing Oxygen Molecules Different from that Utilizing Oxygen Radicals. ECS Transactions, 2012, 45, 453-460.	0.5	0
85	Statistical analysis of Random Telegraph Noise reduction effect by separating channel from the interface. , 2012, , .		25
86	A Simple Test Structure for Evaluating the Variability in Key Characteristics of a Large Number of MOSFETs. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 145-154.	1.7	5
87	A Test Circuit for Statistical Evaluation of p-n Junction Leakage Current and its Noise. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 303-309.	1.7	3
88	A test circuit for extremely low gate leakage current measurement of 10 aA for 80,000 MOSFETs in 80 s. , 2012, , .		3
89	A novel chemically, thermally and electrically robust Cu interconnect structure with an organic non-porous ultralow-k dielectric fluorocarbon (k=2.2). , 2012, , .		1
90	The role of the temperature on the scattering mechanisms limiting the electron mobility in metal-oxide-semiconductor field-effect-transistors fabricated on (110) silicon-oriented wafers. , 2012, , .		4

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91	Densification of chemical vapor deposition silicon dioxide film using oxygen radical oxidation. Journal of Applied Physics, 2012, 111, 034101.	2.5	13
92	Cu Single Damascene Integration of an Organic Nonporous Ultralow- $k$ Fluorocarbon Dielectric Deposited by Microwave-Excited Plasma-Enhanced CVD. IEEE Transactions on Electron Devices, 2012, 59, 1445-1453.	3.0	5
93	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	1.5	3
94	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	1.5	2
95	High Integrity SiO <sub>2</sub> Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaIn/GaN Hybrid Metal-Oxide-Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	1.5	4
96	Hole Mobility in Accumulation Mode Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DC07.	1.5	2
97	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow- $k$ Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	1.5	1
98	Formation speed of atomically flat surface on Si (100) in ultra-pure argon. Microelectronic Engineering, 2011, 88, 3133-3139.	2.4	14
99	Evaluation for Anomalous Stress-Induced Leakage Current of Gate $\text{SiO}_2$ Films Using Array Test Pattern. IEEE Transactions on Electron Devices, 2011, 58, 3307-3313.	3.0	8
100	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	1.5	4
101	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metal-Oxide-Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	1.5	21
102	Tribological Effects of Brush Scrubbing in Post Chemical Mechanical Planarization Cleaning on Electrical Characteristics in Novel Non-porous Low- $k$ Dielectric Fluorocarbon on Cu Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EC07.	1.5	9
103	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	4
104	Analysis of the Low-Frequency Noise Reduction in Si(100) Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	1.5	6
105	Highly Reliable Radical SiO <sub>2</sub> Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	1.5	5
106	Electrical Characteristics of Novel Non-porous Low- $k$ Dielectric Fluorocarbon on Cu Interconnects for 22 nm Generation and Beyond. Japanese Journal of Applied Physics, 2011, 50, 05EB02.	1.5	7
107	Tribological Study of Brush Scrubbing in Post-Chemical Mechanical Planarization Cleaning in Non-porous Ultralow- $k$ Dielectric-Cu Interconnects. Journal of the Electrochemical Society, 2011, 158, H1145.	2.9	13
108	Cu damascene interconnects with an organic low- $k$ fluorocarbon dielectric deposited by microwave excited plasma enhanced CVD. , 2011, , .		1

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109	(Invited) High Power Normally-Off GaN MOSFET. ECS Transactions, 2011, 41, 87-100.	0.5	4
110	Gate SiO <sub>2</sub> Film Integrity on Ultra-Pure Argon Anneal (100) Silicon Surface. ECS Transactions, 2011, 41, 147-156.	0.5	6
111	Advanced Direct-Polish Process on Organic Non-Porous Ultra Low-k Fluorocarbon Dielectric on Cu Interconnects. ECS Transactions, 2011, 34, 653-658.	0.5	5
112	Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. Electrochemical and Solid-State Letters, 2011, 14, H351.	2.2	8
113	Understanding of traps causing random telegraph noise based on experimentally extracted time constants and amplitude. , 2011, , .		26
114	1/f CHANNEL NOISE AT HIGH DRAIN CURRENT IN MOS TRANSISTORS. Fluctuation and Noise Letters, 2011, 10, 431-445.	1.5	6
115	Different Properties of Erbium Silicides on Si(100) and Si(551) Orientation Surfaces. ECS Transactions, 2011, 41, 365-373.	0.5	0
116	Clear Difference between the Chemical Structure of SiO <sub>2</sub> /Si Interfaces Formed Using Oxygen Radicals versus Oxygen Molecules. ECS Transactions, 2011, 35, 115-122.	0.5	1
117	Pr <sub>3</sub> Si <sub>6</sub> N <sub>11</sub> /Si <sub>3</sub> N <sub>4</sub> Stacked High-k Gate Dielectrics with High Quality Ultrathin Si <sub>3</sub> N <sub>4</sub> Interfacial Layers. ECS Transactions, 2011, 35, 275-284.	0.5	1
118	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	1.5	10
119	Analysis of the Low-Frequency Noise Reduction in Si(100) Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	1.5	3
120	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	5
121	Tribological Effects of Brush Scrubbing in Post Chemical Mechanical Planarization Cleaning on Electrical Characteristics in Novel Non-porous Low-k Dielectric Fluorocarbon on Cu Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EC07.	1.5	3
122	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	1.5	3
123	Highly Reliable Radical SiO <sub>2</sub> Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	1.5	2
124	Mesoscopic-Scale and Small Strain Field beneath SiO <sub>2</sub> /Si Interface Revealed by a Multiple-Wave X-ray Diffraction Phenomenon - Depth of the Strain Field. E-Journal of Surface Science and Nanotechnology, 2011, 9, 47-50.	0.4	0
125	Electrical Characteristics of Novel Non-porous Low-k Dielectric Fluorocarbon on Cu Interconnects for 22 nm Generation and Beyond. Japanese Journal of Applied Physics, 2011, 50, 05EB02.	1.5	1
126	Statistical Evaluation of Process Damage Using an Arrayed Test Pattern in a Large Number of MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 1310-1318.	3.0	12



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127	Relation Between the Mobility, $\frac{1}{f}$ Noise, and Channel Direction in MOSFETs Fabricated on (100) and (110) Silicon-Oriented Wafers. IEEE Transactions on Electron Devices, 2010, 57, 1597-1607.	3.0	24
128	Characterization of MgZnO films grown by plasma enhanced metal-organic chemical vapor deposition. Thin Solid Films, 2010, 518, 2953-2956.	1.8	17
129	Modelling of the hole mobility in p-channel MOS transistors fabricated on (1 1 0) oriented silicon wafers. Solid-State Electronics, 2010, 54, 420-426.	1.4	18
130	Impact of Work Function Optimized S/D Silicide Contact for High Current Drivability CMOS. ECS Transactions, 2010, 28, 315-324.	0.5	2
131	Crystallographic orientation dependence of compositional transition and valence band offset at SiO <sub>2</sub> /Si interface formed using oxygen radicals. Applied Physics Letters, 2010, 96, 173103.	3.3	8
132	Ultra-low series resistance W/ErSi <sub>2</sub> /n <sup>+</sup> -Si and W/Pd <sub>2</sub> /Si/p <sup>+</sup> -Si S/D electrodes for advanced CMOS platform. , 2010, , .		4
133	Atomically Flattening Technology at 850Å°C for Si(100) Surface. ECS Transactions, 2010, 28, 299-309.	0.5	28
134	Very High Performance CMOS on Si(551) Using Radical Oxidation Technology and Accumulation-Mode SOI Device Structure. Journal of the Electrochemical Society, 2010, 157, H389.	2.9	9
135	Evaluation of Narrow Gap Filling Ability in Shallow Trench Isolation by Organosiloxane Sol-Gel Precursor. ECS Transactions, 2010, 33, 135-143.	0.5	3
136	Low Contact Resistivity with Low Silicide/p <sup>+</sup> -Silicon Schottky Barrier for High-Performance p-Channel Metalâ€“Oxideâ€“Silicon Field Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 04DA03.	1.5	8
137	Experimental Investigation of Effect of Channel Doping Concentration on Random Telegraph Signal Noise. Japanese Journal of Applied Physics, 2010, 49, 04DC07.	1.5	19
138	Depth Profile of Nitrogen Atoms in Silicon Oxynitride Films Formed by Low-Electron-Temperature Microwave Plasma Nitridation. Japanese Journal of Applied Physics, 2010, 49, 091301.	1.5	8
139	Analysis of Hundreds of Time Constant Ratios and Amplitudes of Random Telegraph Signal with Very Large Scale Array Test Pattern. Japanese Journal of Applied Physics, 2010, 49, 04DC06.	1.5	12
140	End-Point Detection of Ta/TaN Chemical Mechanical Planarization via Forces Analysis. Japanese Journal of Applied Physics, 2010, 49, 05FC01.	1.5	20
141	Light-Emitting Diode Based on ZnO by Plasma-Enhanced Metalâ€“Organic Chemical Vapor Deposition Employing Microwave Excited Plasma. Japanese Journal of Applied Physics, 2010, 49, 04DG14.	1.5	5
142	A test structure for statistical evaluation of pn junction leakage current based on CMOS image sensor technology. , 2010, , .		3
143	Statistical evaluation of dynamic junction leakage current fluctuation using a simple arrayed capacitors circuit. , 2010, , .		3
144	Statistical evaluation for trap energy level of RTS characteristics. , 2010, , .		10

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145	Electrical Properties of Metal-Oxide-Containing SiO <sub>2</sub> Films Formed by Organosiloxane Sol-Gel Precursor. Japanese Journal of Applied Physics, 2010, 49, 111503.	1.5	1
146	Hole Mobility in Si(110) p-MOS Transistors. ECS Transactions, 2009, 16, 7-12.	0.5	1
147	In situ Observation of Grain Growth on Electroplated Cu Film by Electron Backscatter Diffraction. Japanese Journal of Applied Physics, 2009, 48, 066507.	1.5	14
148	Impact of New Approach to Improve MOSFETs Performance with Ultrathin Gate Insulator. ECS Transactions, 2009, 19, 65-70.	0.5	0
149	Three-Step Room Temperature Wet Cleaning Process for Silicon Substrate. Solid State Phenomena, 2009, 145-146, 189-192.	0.3	1
150	Effect of Polisher Kinematics in Reducing Average and Variance of Shear Force and Increasing Removal Rate in Copper CMP. ECS Transactions, 2009, 18, 465-471.	0.5	0
151	Three-Step Room-Temperature Cleaning of Bare Silicon Surface for Radical-Reaction-Based Semiconductor Manufacturing. Journal of the Electrochemical Society, 2009, 156, H10.	2.9	8
152	Different Types of Degradation and Recovery Mechanisms on NBT Stress for Thin SiO <sub>2</sub> Films by On-The-Fly Measurement. ECS Transactions, 2009, 19, 339-350.	0.5	0
153	Stress-induced leakage current and random telegraph signal. Journal of Vacuum Science & Technology B, 2009, 27, 435.	1.3	5
154	The electric properties of low-magnetic-loss magnetic composites containing Zn-Ni-Fe particles. Journal of Physics Condensed Matter, 2009, 21, 436009.	1.8	13
155	Complementary Metal-Oxide-Silicon Field-Effect-Transistors Featuring Atomically Flat Gate Insulator Film/Silicon Interface. Japanese Journal of Applied Physics, 2009, 48, 04C048.	1.5	28
156	Deposition of Microcrystalline Si <sub>1-x</sub> Gex by RF Magnetron Sputtering on SiO <sub>2</sub> Substrates. Japanese Journal of Applied Physics, 2009, 48, 04C124.	1.5	1
157	Anomalous Random Telegraph Signal Extractions from a Very Large Number of n-Metal Oxide Semiconductor Field-Effect Transistors Using Test Element Groups with 0.47 Hz-3.0 MHz Sampling Frequency. Japanese Journal of Applied Physics, 2009, 48, 04C044.	1.5	12
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